

SANYO

No.3665

2SC4769

NPN Triple Diffused Planar Silicon Transistor
 Very High-Definition Color Display
 Horizontal Deflection Output Applications

Features

- High-speed ($t_f = 100\text{ns typ}$)
- High breakdown voltage ($V_{CBO} = 1500\text{V}$)
- High reliability (Adoption of HVP process)
- Adoption of MBIT process
- On-chip damper diode

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

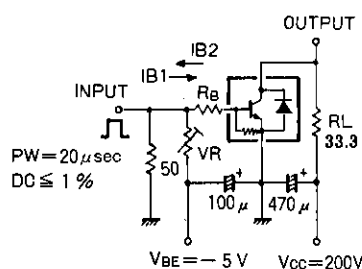
			unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current	I_C	7	A
Peak Collector Current	i_{cp}	16	A
Collector Dissipation	P_C	3	W
		60	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

 $T_c = 25^\circ\text{C}$ **Electrical Characteristics at $T_a = 25^\circ\text{C}$**

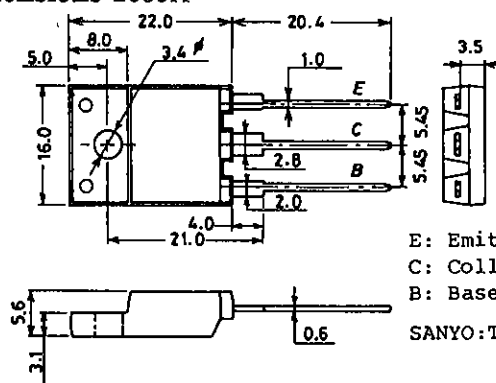
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800\text{V}, I_E = 0$			10	μA
Collector Cutoff Current	I_{CES}	$V_{CE} = 1500\text{V}, R_{BE} = 0$			1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C = 100\text{mA}, I_B = 0$	800			V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$	40		130	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 5\text{A}, I_B = 1.7\text{A}$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 5\text{A}, I_B = 1.7\text{A}$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	8			
	$h_{FE(2)}$	$V_{CE} = 5\text{V}, I_C = 5\text{A}$	3.0*		8.0*	
Diode Forward Voltage	V_F	$I_{EC} = 7\text{A}$			2.0	V
Storage Time	t_{stg}	$I_C = 4\text{A}, I_{B1} = 0.8\text{A}$			3.0	μs
Fall Time	t_f	$I_{B2} = -1.6\text{A}$	0.1	0.2		μs

* : The 2SC4769 is classified by 5A h_{FE} as follows :

h_{FE}	3 to 5	4 to 6	5 to 8
Rank	1	2	3

Switching Time Test CircuitUnit (resistance: Ω , capacitance: F)**Package Dimensions 2039A**

(unit: mm)



E: Emitter
 C: Collector
 B: Base

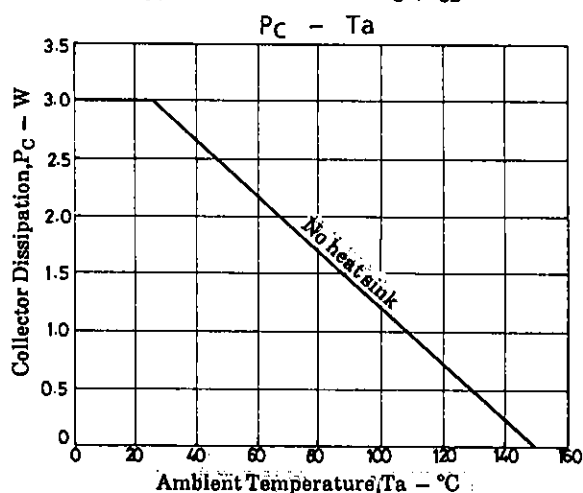
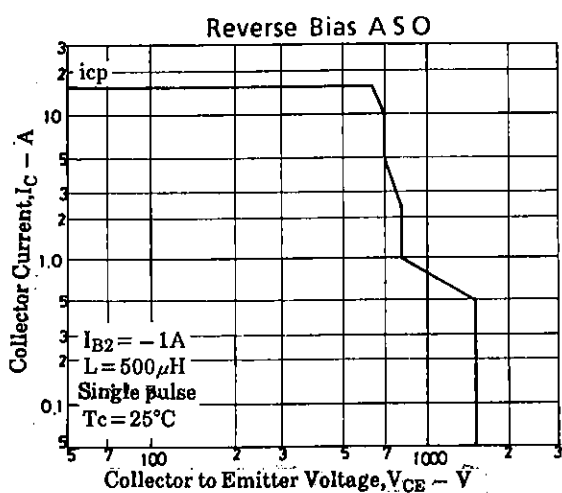
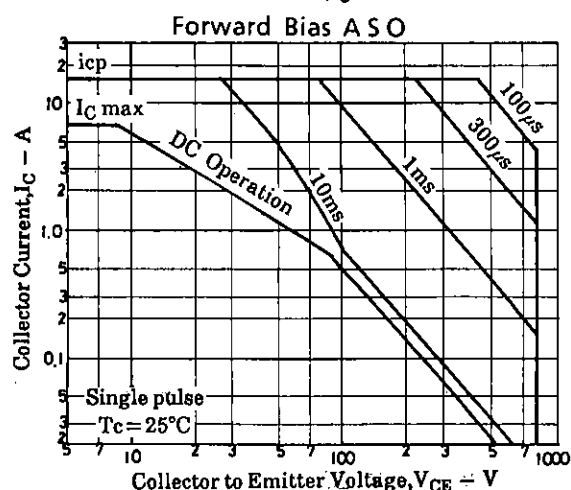
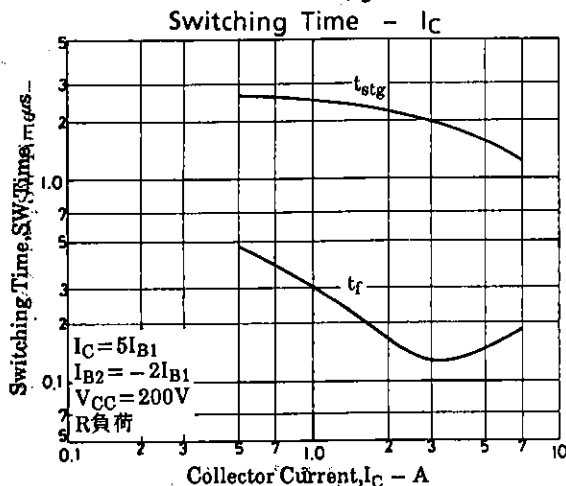
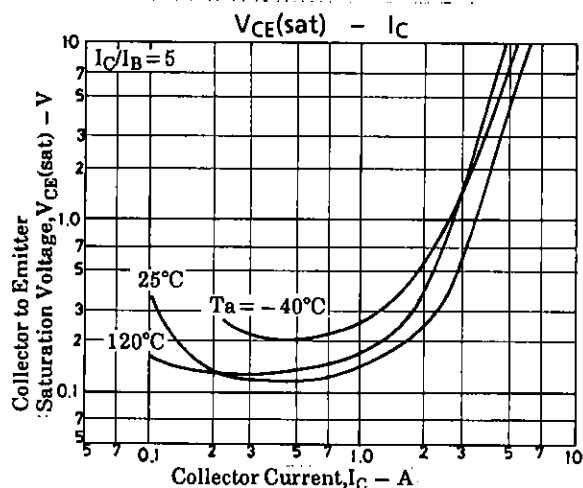
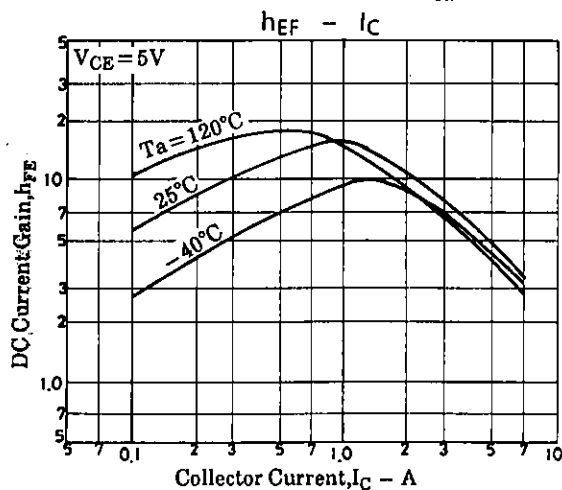
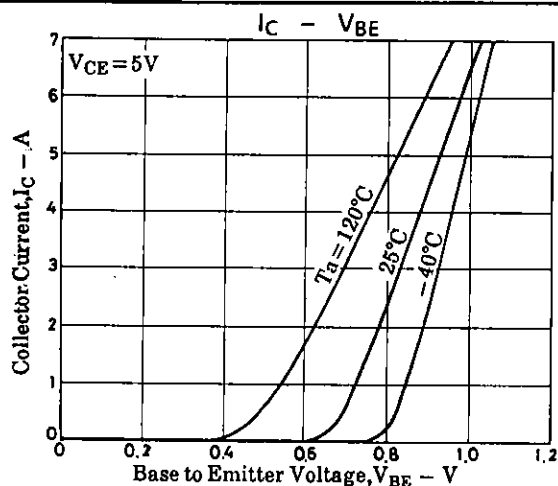
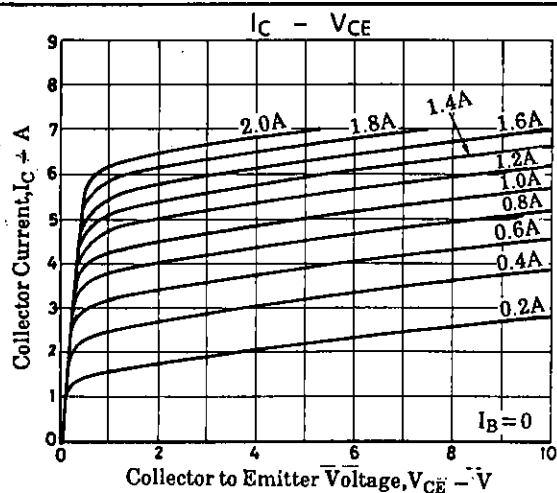
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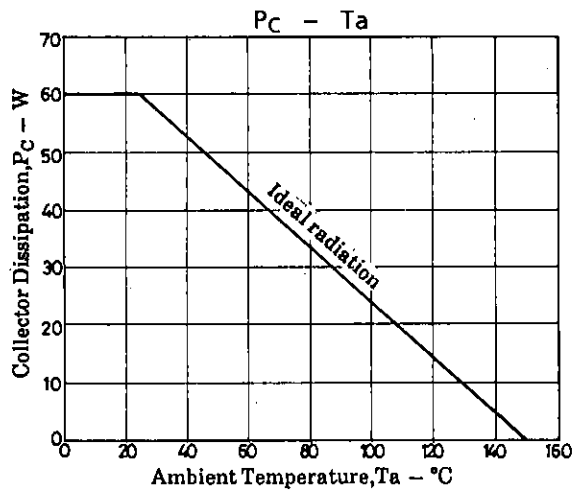
N130MH, JK(KOTO) No.3665-1/3

2SC4769



No.3665-2/3

2SC4769



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